



Insulated Gate Bipolar Transistor (Ultrafast IGBT), 75 A



SOT-227

FEATURES

- NPT Generation V IGBT technology
- Square RBSOA
- Positive $V_{CE(on)}$ temperature coefficient
- Fully isolated package
- Speed 8 kHz to 60 kHz
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRODUCT SUMMARY	
V_{CES}	1200 V
I_C DC	75 A at 95 °C
$V_{CE(on)}$ typical at 75 A, 25 °C	3.3 V
Package	SOT-227

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting on heatsink
- Plug-in compatible with other SOT-227 packages
- Low EMI, requires less snubbing

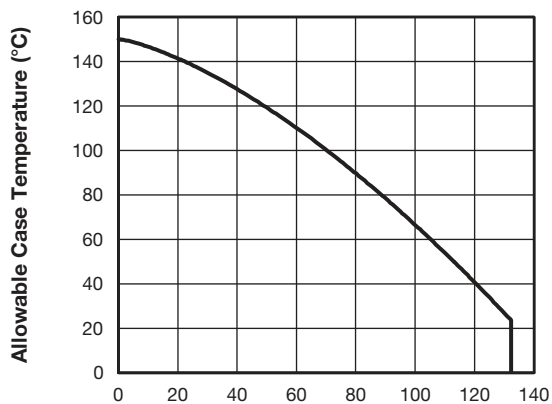
ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25$ °C	131	A
		$T_C = 80$ °C	89	
Pulsed collector current	I_{CM}		200	
Clamped inductive load current	I_{LM}		200	
Gate to emitter voltage	V_{GE}		± 20	V
Power dissipation	P_D	$T_C = 25$ °C	658	W
		$T_C = 80$ °C	369	
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0$ V, $I_C = 250$ μ A	1200	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15$ V, $I_C = 75$ A	-	3.3	3.8	
		$V_{GE} = 15$ V, $I_C = 75$ A, $T_J = 125$ °C	-	3.6	3.9	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 250$ μ A	4	5	6	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 1$ mA (25 °C to 125 °C)	-	- 12	-	mV/°C
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0$ V, $V_{CE} = 1200$ V	-	3	250	μ A
		$V_{GE} = 0$ V, $V_{CE} = 1200$ V, $T_J = 150$ °C	-	4	20	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20$ V	-	-	± 200	nA



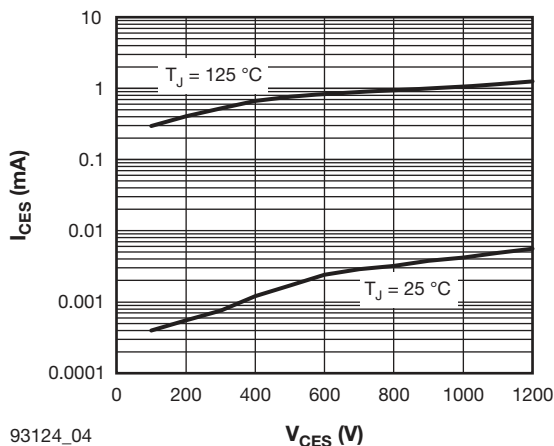
SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 50\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$		-	690	-	nC
Gate to emitter charge (turn-on)	Q_{ge}			-	65	-	
Gate to collector charge (turn-on)	Q_{gc}			-	250	-	
Turn-on switching loss	E_{on}	$I_C = 75\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $R_g = 5\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$	Energy losses include tail and diode recovery (see fig. 18)	-	1.53	-	mJ
Turn-off switching loss	E_{off}			-	1.76	-	
Total switching loss	E_{tot}			-	3.29	-	
Turn-on switching loss	E_{on}	-		2.49	-		
Turn-off switching loss	E_{off}	-		3.45	-		
Total switching loss	E_{tot}	-		5.94	-		
Turn-on delay time	$t_{d(on)}$	$I_C = 75\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $R_g = 5\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $T_J = 125\text{ }^\circ\text{C}$		-	281	-	ns
Rise time	t_r			-	45	-	
Turn-off delay time	$t_{d(off)}$			-	300	-	
Fall time	t_f		-	126	-		
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}$, $I_C = 200\text{ A}$, $R_g = 22\text{ }\Omega$, $V_{GE} = 15\text{ V}$ to 0 V , $V_{CC} = 900\text{ V}$, $V_P = 1200\text{ V}$, $L = 500\text{ }\mu\text{H}$		Fullsquare			

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL		MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J , T_{STG}		- 40	-	150	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to case	R_{thJC}		-	-	0.19	
Thermal resistance case to heatsink	R_{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	-	1.3	Nm
Case style			SOT-227			



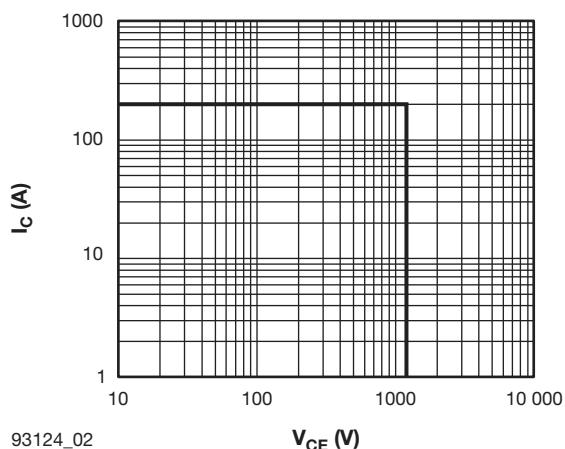
93124_01 **I_C - Continuous Collector Current (A)**

Fig. 1 - Maximum DC IGBT Collector Current vs. Case Temperature



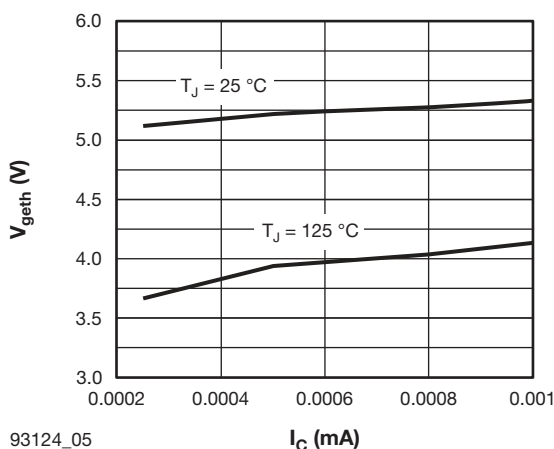
93124_04 **V_{CE(S)} (V)**

Fig. 4 - Typical IGBT Zero Gate Voltage Collector Current



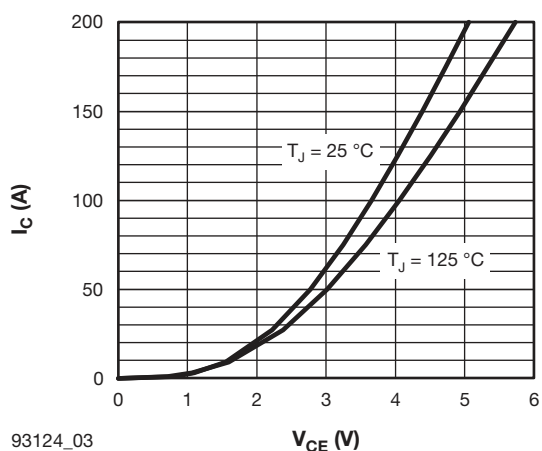
93124_02 **V_{CE} (V)**

Fig. 2 - IGBT Reverse Bias SOA
 $T_J = 150\text{ °C}$, $V_{GE} = 15\text{ V}$



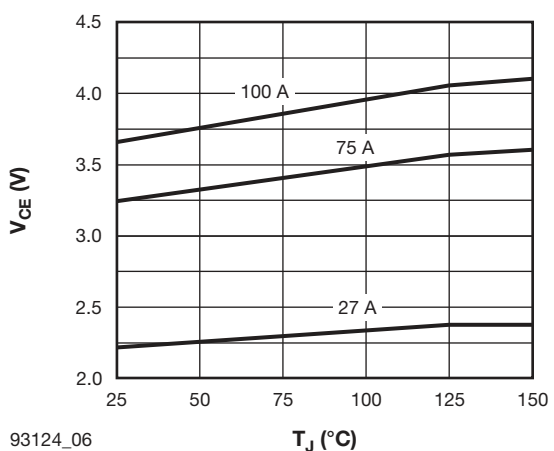
93124_05 **I_C (mA)**

Fig. 5 - Typical IGBT Threshold Voltage



93124_03 **V_{CE} (V)**

Fig. 3 - Typical IGBT Collector Current Characteristics



93124_06 **T_J (°C)**

Fig. 6 - Typical IGBT Collector to Emitter Voltage vs. Junction Temperature, $V_{GE} = 15\text{ V}$

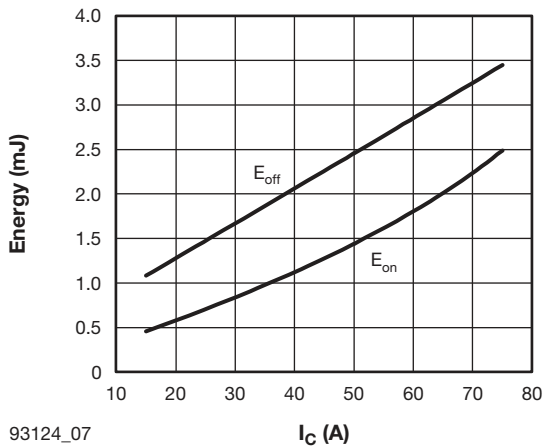


Fig. 7 - Typical IGBT Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$, $L = 500\ \mu\text{H}$, $V_{CC} = 600\ \text{V}$,
 $R_g = 5\ \Omega$, $V_{GE} = 15\ \text{V}$

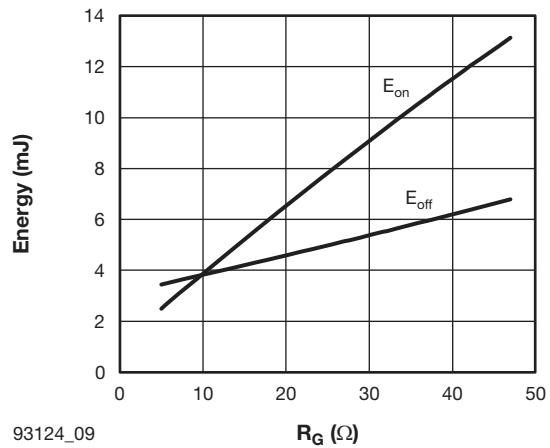


Fig. 9 - Typical IGBT Energy Loss vs. R_G
 $T_J = 125^\circ\text{C}$, $I_C = 75\ \text{A}$, $L = 500\ \mu\text{H}$,
 $V_{CC} = 600\ \text{V}$, $V_{GE} = 15\ \text{V}$

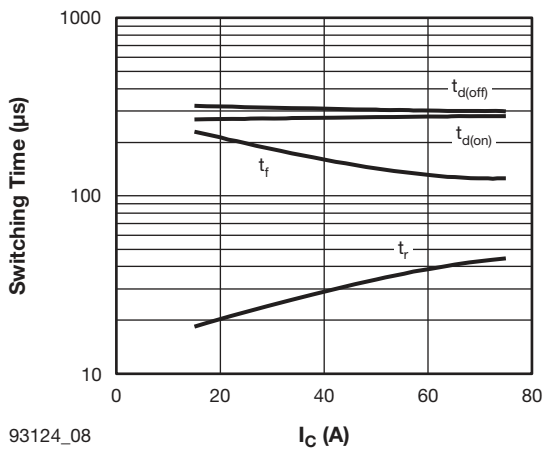


Fig. 8 - Typical IGBT Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$, $L = 500\ \mu\text{H}$, $V_{CC} = 600\ \text{V}$,
 $R_g = 5\ \Omega$, $V_{GE} = 15\ \text{V}$

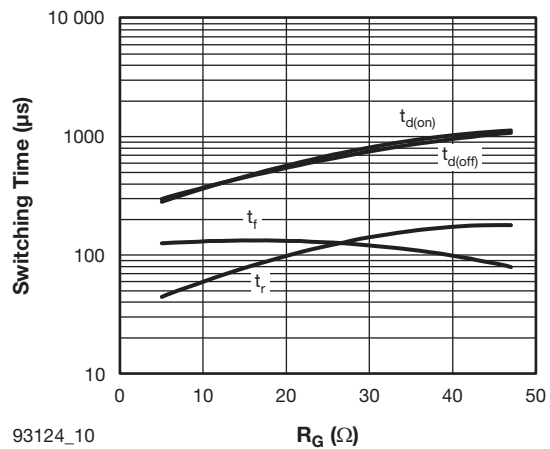


Fig. 10 - Typical IGBT Switching Time vs. R_G
 $T_J = 125^\circ\text{C}$, $L = 500\ \mu\text{H}$, $V_{CC} = 600\ \text{V}$,
 $R_g = 5\ \Omega$, $V_{GE} = 15\ \text{V}$

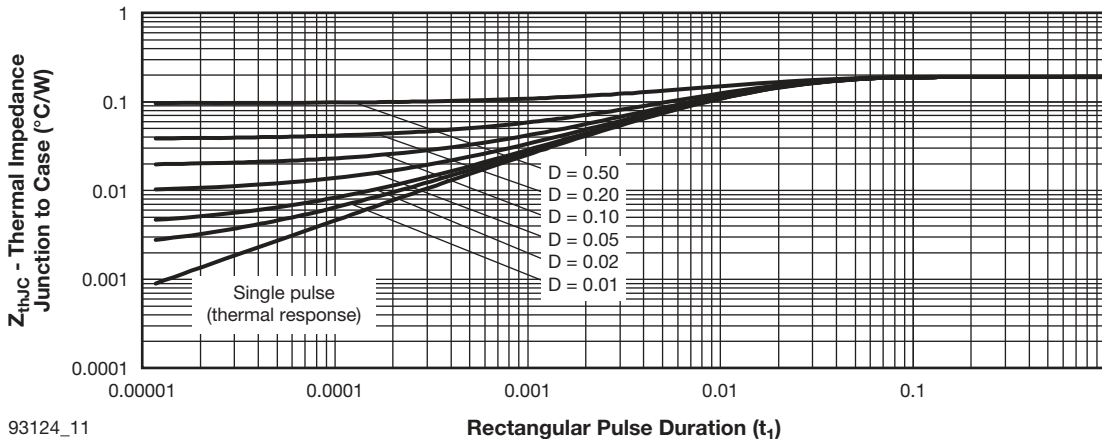
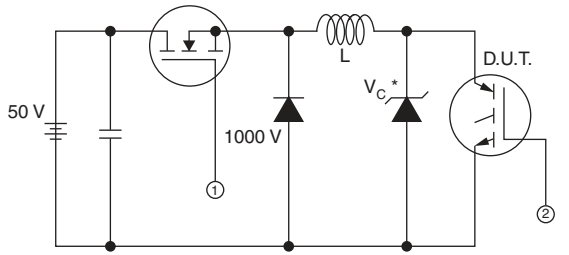


Fig. 11 - Maximum Thermal Impedance Z_{thJC} Characteristics



* Driver same type as D.U.T.; $V_C = 80\%$ of $V_{ce(max)}$
 * Note: Due to the 50 V power supply, pulse width and inductor will increase to obtain I_d

Fig. 12 - Clamped Inductive Load Test Circuit

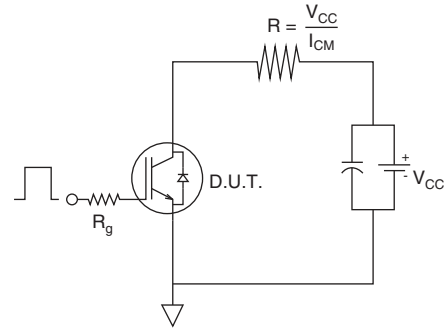


Fig. 13 - Pulsed Collector Current Test Circuit

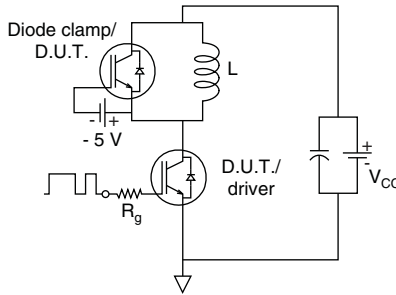


Fig. 14 - Switching Loss Test Circuit

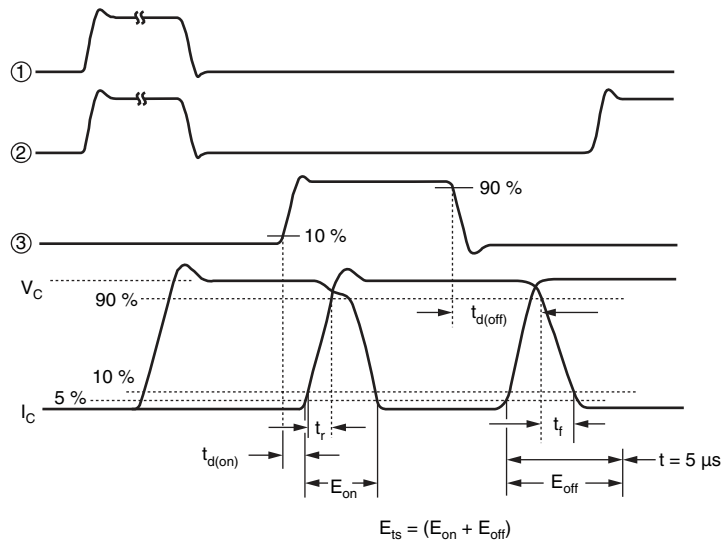
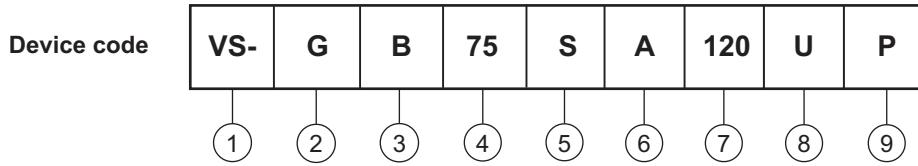


Fig. 15 - Switching Loss Waveforms Test Circuit

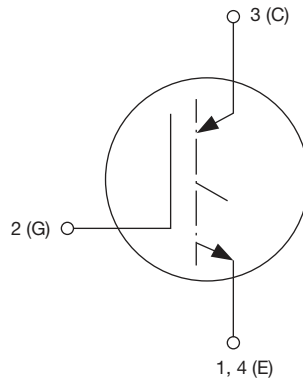


ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Insulated Gate Bipolar Transistor (IGBT)
- 3** - B = IGBT Generation 5
- 4** - Current rating (75 = 75 A)
- 5** - Circuit configuration (S = Single switch without antiparallel diode)
- 6** - Package indicator (A = SOT-227)
- 7** - Voltage rating (120 = 1200 V)
- 8** - Speed/type (U = Ultrafast IGBT)
- 9** - Totally lead (Pb)-free

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95036
Packaging information	www.vishay.com/doc?95037



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